Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (Currently Amended) A method for forming a silicon film, comprising:

 applying by patterning providing an ink composition containing comprising a

 silicon compound onto a substrate by an ink jet process, wherein

 the silicon compound having at least one cyclic structure is represented by

 SinXm, n representing an integer of 3 or more, m representing an integer of n, 2n-2, 2n, or

 2n+2, and X representing a hydrogen atom and/or a halogen atom, and

 the ink composition to be provided onto the substrate has a surface tension of

 20 to 70 dyn/cm for preventing non-linear flight of ink when emitted, and for retaining a

 stable meniscus shape in an ink-jet nozzle.
- 2. (Previously Presented) The method for forming a silicon film according to claim 1, the ink composition being applied in an inert atmosphere.
- 3. (Previously Presented) The method for forming a silicon film according to claim 1, further comprising: a drying step of removing a solvent of the composition; and a step of pyrolyzing and/or photolyzing in the coating film.
- 4. (Previously Presented) The method for forming a silicon film according to claim 3, further comprising:

a step for irradiating the silicon film formed by heat treatment and/or light treatment with laser to convert the amorphous silicon film into a polycrystalline silicon film.

- 5. (Cancelled)
- 6. (Currently Amended) The A method for forming a silicon film according to elaim 1 comprising:

applying by patterning an ink composition containing a silicon compound onto

a substrate by an ink jet process, the silicon compound having at least one cyclic structure,

the silicon compound is a silicon compound represented by

$$Si_aX_bY_c$$

X representing a hydrogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to 2a+c, and c representing an integer of 1 to a.

7. (Currently Amended) The A method for forming a silicon film according to elaim 1 comprising:

applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process, the silicon compound having at least one cyclic structure, the silicon compound is a composition containing a silicon compound represented by the following general formula and a silicon compound represented by

$$Si_nX_m$$

n representing an integer of 3 or more, m representing an integer of n, 2n-2, or 2n, and X representing a hydrogen atom and/or a halogen atom; and

silicon compound represented by

$$Si_aX_bY_c$$

X representing a hydrogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to 2a+c, and c representing an integer of 1 to a, at least one of the compounds satisfying one of the formulae is cyclic.

8. (Currently Amended) The method for forming a silicon film according to claim-5_1, n being in a range of 5 to 20.

- 9. (Previously Presented) The method for forming a silicon film according to claim 6, a+c being in a range of 5 to 20.
- 10. (Previously Presented) The method for forming a silicon film according to claim 1, the silicon compound being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.
- 11. (Previously Presented) The method for forming a silicon film according to claim 10, the solvent being a hydrocarbon solvent.
- 12. (Previously Presented) The method for forming a silicon film according to claim 1, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight.
- 13. (Currently Amended) The method for forming a silicon film according claim 1, the composition having a viscosity of 1 to 50 mPa·s-and a surface tension of 20 to 70 dyn/em.
- 14. (Currently Amended) An ink-jet ink composition for forming a silicon film, comprising:

a silicon compound represented

$$Si_nX_m$$

n representing an integer of 3 or more, m representing an integer of n, 2n–2, 2n, or 2n+2, and X representing a hydrogen atom and/or a halogen atom, the silicon compound having at least one cyclic structure wherein the ink composition to be provided onto the substrate has a surface tension of 20 to 70 dyn/cm for preventing non-linear flight of ink when emitted, and for retaining a stable meniscus shape in an ink-jet nozzle.

15. (Previously Presented) An ink-jet ink composition for forming a silicon film, comprising:

a silicon compound represented by

$$Si_aX_bY_c$$

X representing a hydrogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to 2a+c, and c representing an integer of 1 to a, the silicon compound having at least one cyclic structure.

16. (Previously Presented) An ink-jet ink composition for forming a silicon film, comprising:

a silicon compound represented by

$$Si_nX_m$$

n representing an integer of 3 or more, m representing an integer of n, 2n-2, or 2n, and X representing a hydrogen atom and/or a halogen atom; and

a silicon compound represented by

$$Si_aX_bY_c$$
 (II)

X representing a hydrogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to 2a+c, and c representing an integer of 1 to a.

- 17. (Previously Presented) The ink composition according to claim 14, n being in a range of 5 to 20.
- 18. (Previously Presented) The ink composition according to claim 15, wherein a+c being in a range of 5 to 20.
- 19. (Previously Presented) The ink composition according to claim 14, the silicon compound being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.
- 20. (Previously Presented) The ink composition according to claim 19, the solvent being a hydrocarbon solvent.

- 21. (Previously Presented) The ink composition according to claim 14, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight.
- 22. (Currently Amended) The ink composition according to claim 14, the composition having a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.
 - 23. (Cancelled)